

# 128Mbit DDR SDRAM

*2M x 16Bit x 4 Banks*  
*Double Data Rate Synchronous DRAM*

**Revision 1.2**

**July 2003**

Samsung Electronics reserves the right to change products or specification without notice.

## K4D261638E

## 128M DDR SDRAM

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### Revision History

#### Revision 1.2 (July 21, 2003)

- Added K4D261638E-TC2A in the spec

#### Revision 1.1 (January 16, 2003)

- Changed ICC6 from 2mA to 4mA
- Changed ICC5 of K4D261638E-TC33 from 260mA to 320mA
- Changed ICC5 of K4D261638E-TC36 from 250mA to 310mA
- Changed ICC5 of K4D261638E-TC40 from 230mA to 290mA
- Changed ICC5 of K4D261638E-TC50 from 210mA to 270mA

#### Revision 1.0 (December 24, 2002)

- Defined DC spec
- Changed tRC of K4D261638E-TC33/36 from 13tCK to 15tCK
- Changed tRFC of K4D261638E-TC33/36 from 15tCK to 17tCK
- Changed tRAS of K4D261638E-TC33/36 from 9tCK to 10tCK
- Changed tRP of K4D261638E-TC33/36 from 4tCK to 5tCK
- Changed tDAL of K4D261638E-TC33/36 from 7tCK to 8tCK

#### Revision 0.3 (December 3, 2002) - *Target Spec*

- Typo corrected

#### Revision 0.2 (November 12, 2002) - *Target Spec*

- Changed tPDEX of K4D261638E-TC33/36/40/50 from 1tCK+tIS to 3tCK+tIS

#### Revision 0.1 (November 7, 2002) - *Target Spec*

- Changed tCK(max) of K4D261638E-TC33 from 4ns to 10ns
- Changed tCK(max) of K4D261638E-TC36 from 6ns to 10ns
- Typo corrected

#### Revision 0.0 (October 28, 2002) - *Target Spec*

- Defined Target Specification

## K4D261638E

## 128M DDR SDRAM

### **2M x 16Bit x 4 Banks Double Data Rate Synchronous DRAM with Bi-directional Data Strobe and DLL**

#### FEATURES

- 2.5V  $\pm$  5% power supply for device operation
- 2.5V  $\pm$  5% power supply for I/O interface
- SSTL\_2 compatible inputs/outputs
- 4 banks operation
- MRS cycle with address key programs
  - Read latency 3, 4 (clock)
  - Burst length (2, 4 and 8)
  - Burst type (sequential & interleave)
- All inputs except data & DM are sampled at the positive going edge of the system clock
- Differential clock input
- No Write-Interrupted by Read Function
- 2 DQS's ( 1DQS / Byte )
- Data I/O transactions on both edges of Data strobe
- DLL aligns DQ and DQS transitions with Clock transition
- Edge aligned data & data strobe output
- Center aligned data & data strobe input
- DM for write masking only
- Auto & Self refresh
- 32ms refresh period (4K cycle)
- 66pin TSOP-II
- Maximum clock frequency up to 350MHz
- Maximum data rate up to 700Mbps/pin

#### ORDERING INFORMATION

Part NO.	Max Freq.	Max Data Rate	Interface	Package
K4D261638E-TC2A	350MHz	700Mbps/pin	SSTL_2	66pin TSOP-II
K4D261638E-TC33	300MHz	600Mbps/pin		
K4D261638E-TC36	275MHz	550Mbps/pin		
K4D261638E-TC40	250MHz	500Mbps/pin		
K4D261638E-TC50	200MHz	400Mbps/pin		

For the K4D261638E-TC2A, VDD & VDDQ = 2.8V $\pm$ 0.1V

#### GENERAL DESCRIPTION

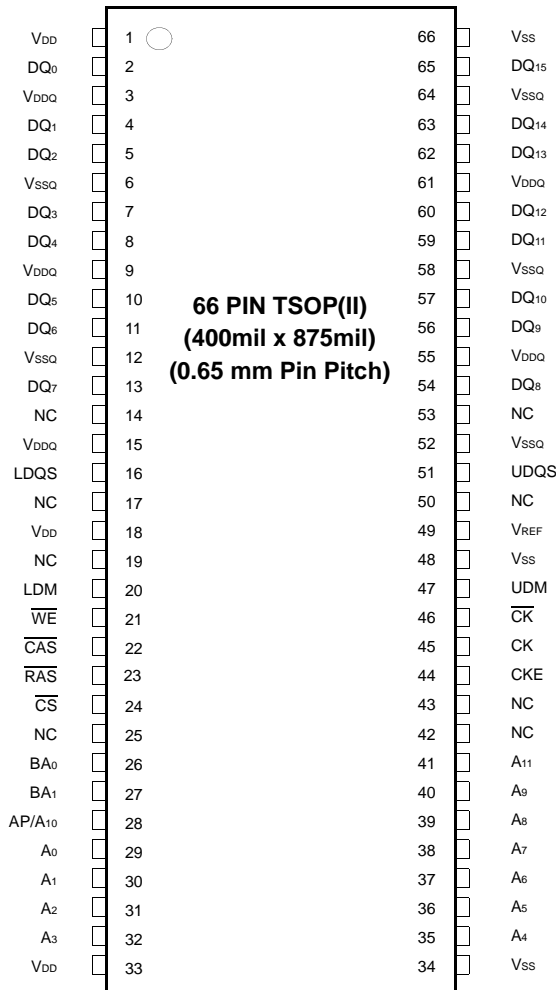
##### FOR 2M x 16Bit x 4 Bank DDR SDRAM

The K4D261638E is 134,217,728 bits of hyper synchronous data rate Dynamic RAM organized as 4 x 2,097,152 words by 16 bits, fabricated with SAMSUNG's high performance CMOS technology. Synchronous features with Data Strobe allow extremely high performance up to 1.4GB/s/chip. I/O transactions are possible on both edges of the clock cycle. Range of operating frequencies, programmable burst length and programmable latencies allow the device to be useful for a variety of high performance memory system applications.

**K4D261638E**

**128M DDR SDRAM**

**PIN CONFIGURATION (Top View)**



**PIN DESCRIPTION**

CK, $\overline{\text{CK}}$	Differential Clock Input	BA0, BA1	Bank Select Address
CKE	Clock Enable	A0 ~A11	Address Input
$\overline{\text{CS}}$	Chip Select	DQ0 ~ DQ15	Data Input/Output
$\overline{\text{RAS}}$	Row Address Strobe	VDD	Power
$\overline{\text{CAS}}$	Column Address Strobe	VSS	Ground
WE	Write Enable	VDDQ	Power for DQ's
L(U)DQS	Data Strobe	VSSQ	Ground for DQ's
L(U)DM	Data Mask	NC	No Connection
RFU	Reserved for Future Use		

**K4D261638E**

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**INPUT/OUTPUT FUNCTIONAL DESCRIPTION**

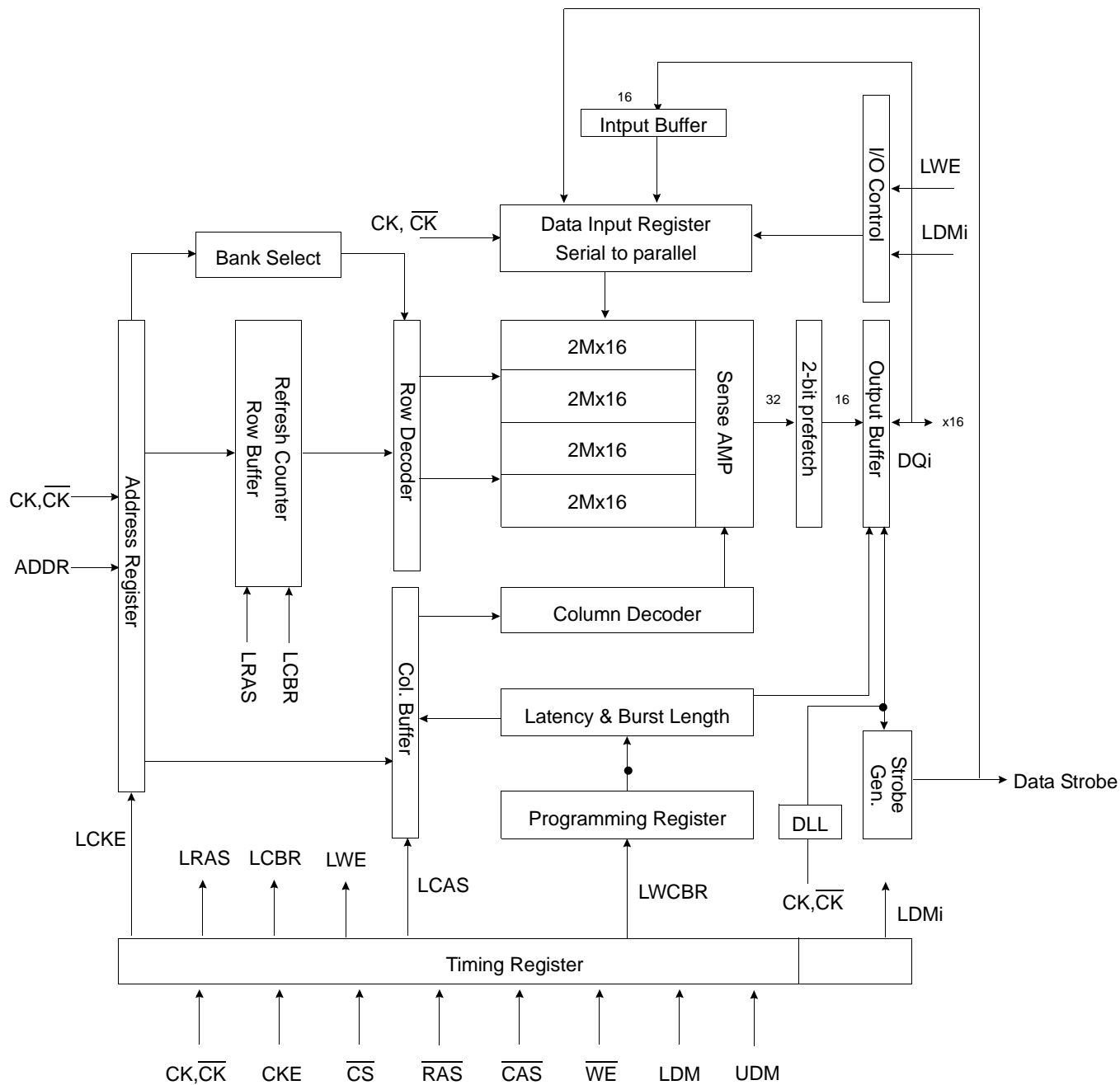
Symbol	Type	Function
CK, $\overline{CK}^*1$	Input	The differential system clock Input. All of the inputs are sampled on the rising edge of the clock except DQ's and DM's that are sampled on both edges of the DQS.
CKE	Input	Activates the CK signal when high and deactivates the $\overline{CK}$ signal when low. By deactivating the clock, CKE low indicates the Power down mode or Self refresh mode.
$\overline{CS}$	Input	$\overline{CS}$ enables the command decoder when low and disabled the command decoder when high. When the command decoder is disabled, new commands are ignored but previous operations continue.
$\overline{RAS}$	Input	Latches row addresses on the positive going edge of the CK with $\overline{RAS}$ low. Enables row access & precharge.
$\overline{CAS}$	Input	Latches column addresses on the positive going edge of the CK with $\overline{CAS}$ low. Enables column access.
$\overline{WE}$	Input	Enables write operation and row precharge. Latches data in starting from $\overline{CAS}$ , $\overline{WE}$ active.
LDQS,UDQS	Input/Output	Data input and output are synchronized with both edge of DQS. For the x16, LDQS corresponds to the data on DQ0-DQ7 ; UDQS corresponds to the data on DQ8-DQ15.
LDM,UDM	Input	Data in Mask. Data In is masked by DM Latency=0 when DM is high in burst write. For the x16, LDM corresponds to the data on DQ0-DQ7 ; UDM corresponds to the data on DQ8-DQ15.
DQ0 ~ DQ15	Input/Output	Data inputs/Outputs are multiplexed on the same pins.
BA0, BA1	Input	Selects which bank is to be active.
A0 ~ A11	Input	Row/Column addresses are multiplexed on the same pins. Row addresses : RA0 ~ RA11, Column addresses : CA0 ~ CA8.
VDD/VSS	Power Supply	Power and ground for the input buffers and core logic.
VDDQ/VSSQ	Power Supply	Isolated power supply and ground for the output buffers to provide improved noise immunity.
VREF	Power Supply	Reference voltage for inputs, used for SSTL interface.
NC/RFU	No connection/ Reserved for future use	This pin is recommended to be left "No connection" on the device

\*1 : The timing reference point for the differential clocking is the cross point of CK and  $\overline{CK}$ .  
For any applications using the single ended clocking, apply VREF to  $\overline{CK}$  pin.

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**128M DDR SDRAM**

**BLOCK DIAGRAM (2Mbit x 16I/O x 4 Bank)**



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**128M DDR SDRAM**

**FUNCTIONAL DESCRIPTION**

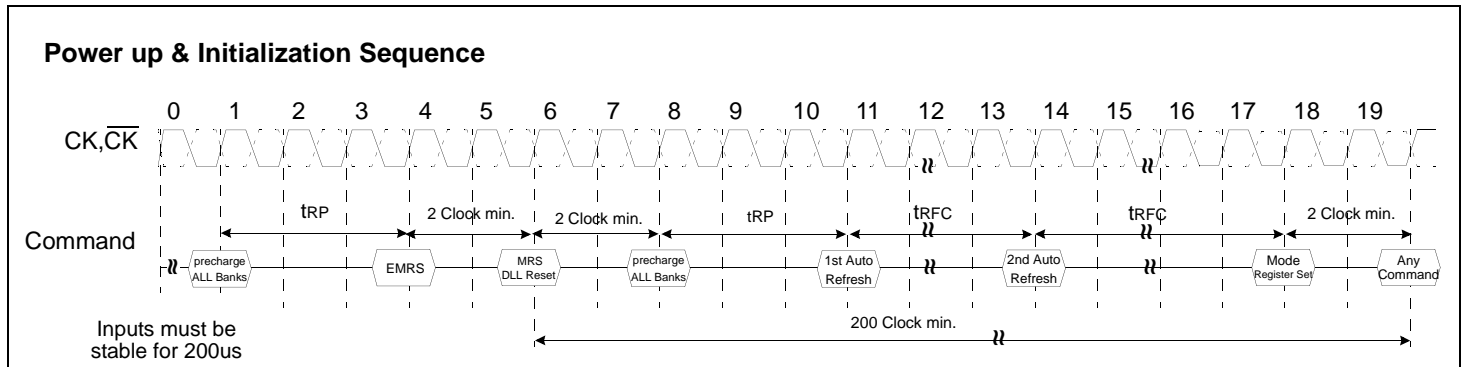
• **Power-Up Sequence**

DDR SDRAMs must be powered up and initialized in a predefined manner to prevent undefined operations.

1. Apply power and keep CKE at low state (All other inputs may be undefined)
  - Apply VDD before VDDQ .
  - Apply VDDQ before VREF & VTT
2. Start clock and maintain stable condition for minimum 200us.
3. The minimum of 200us after stable power and clock(CK,CK<sup>-</sup>), apply NOP and take CKE to be high .
4. Issue precharge command for all banks of the device.
5. Issue a EMRS command to enable DLL
- \*1 6. Issue a MRS command to reset DLL. The additional 200 clock cycles are required to lock the DLL.
- \*1,2 7. Issue precharge command for all banks of the device.
8. Issue at least 2 or more auto-refresh commands.
9. Issue a mode register set command with A8 to low to initialize the mode register.

\*1 The additional 200cycles of clock input is required to lock the DLL after enabling DLL.

\*2 Sequence of 6&7 is regardless of the order.



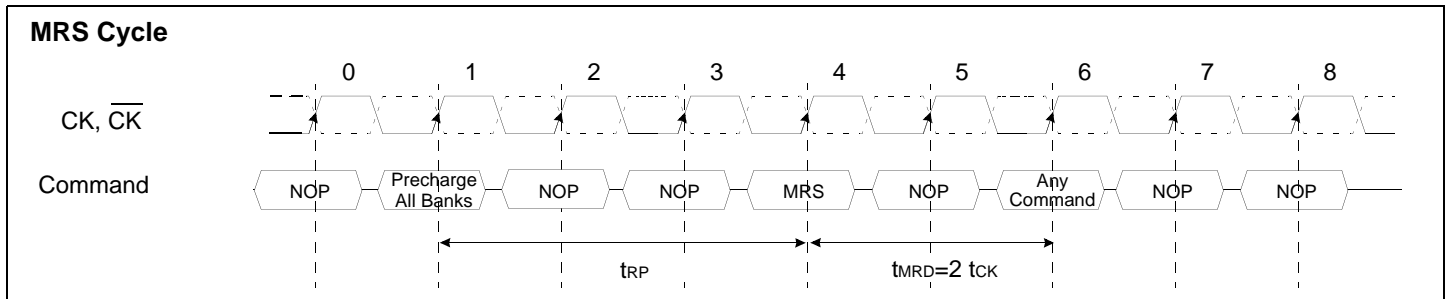
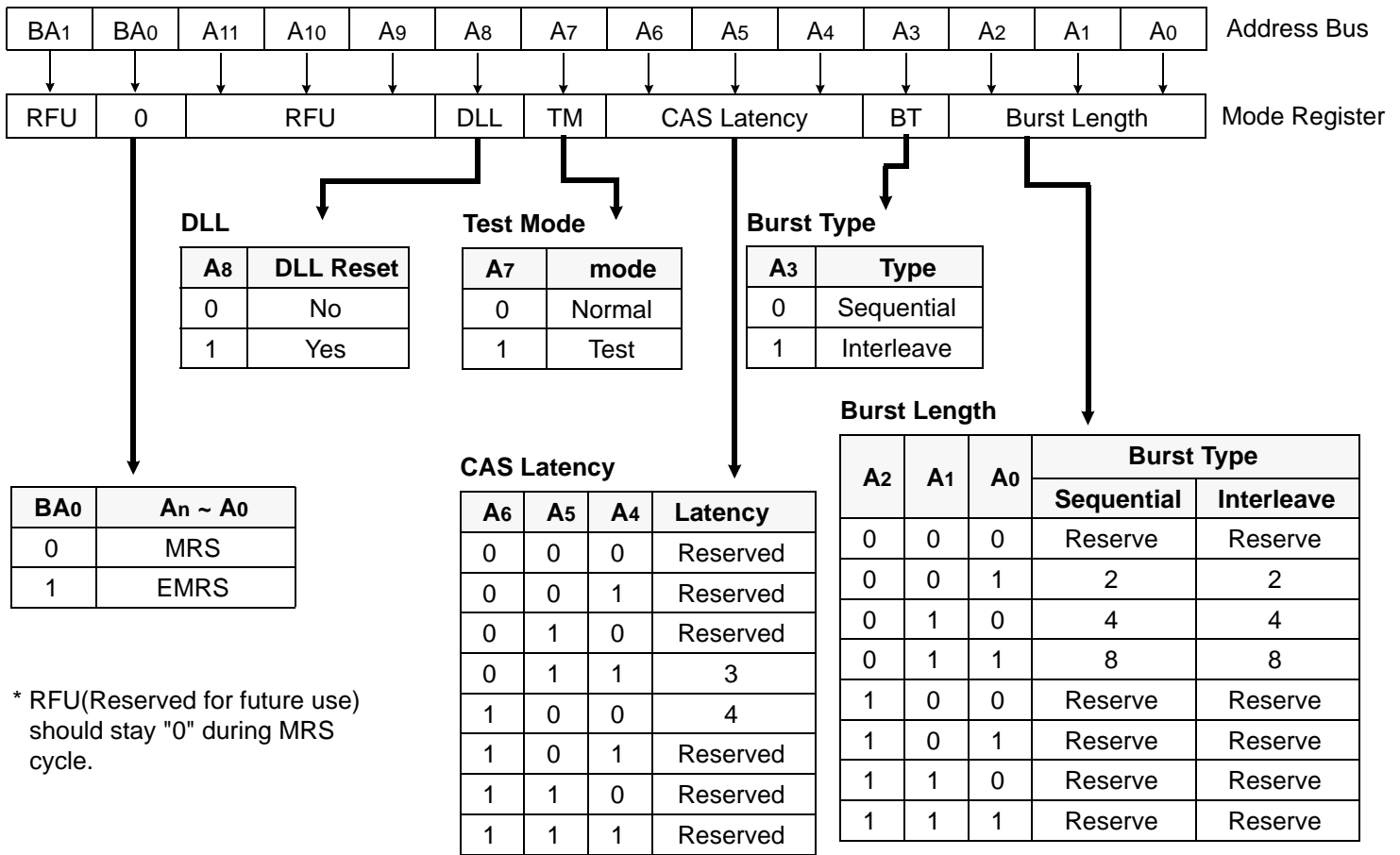
\* When the operating frequency is changed, DLL reset should be required again.  
 After DLL reset again, the minimum 200 cycles of clock input is needed to lock the DLL.

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**MODE REGISTER SET(MRS)**

The mode register stores the data for controlling the various operating modes of DDR SDRAM. It programs CAS latency, addressing mode, burst length, test mode, DLL reset and various vendor specific options to make DDR SDRAM useful for variety of different applications. The default value of the mode register is not defined, therefore the mode register must be written after EMRS setting for proper operation. The mode register is written by asserting low on CS, RAS, CAS and WE(The DDR SDRAM should be in active mode with CKE already high prior to writing into the mode register). The state of address pins A0 ~ A11 and BA0, BA1 in the same cycle as CS, RAS, CAS and WE going low is written in the mode register. Minimum two clock cycles are requested to complete the write operation in the mode register. The mode register contents can be changed using the same command and clock cycle requirements during operation as long as all banks are in the idle state. The mode register is divided into various fields depending on functionality. The burst length uses A0 ~ A2, addressing mode uses A3, CAS latency(read latency from column address) uses A4 ~ A6. A7 is used for test mode. A8 is used for DLL reset. A7,A8, BA0 and BA1 must be set to low for normal MRS operation. Refer to the table for specific codes for various burst length, addressing modes and CAS latencies.



\*1 : MRS can be issued only at all banks precharge state.  
 \*2 : Minimum trp is required to issue MRS command.

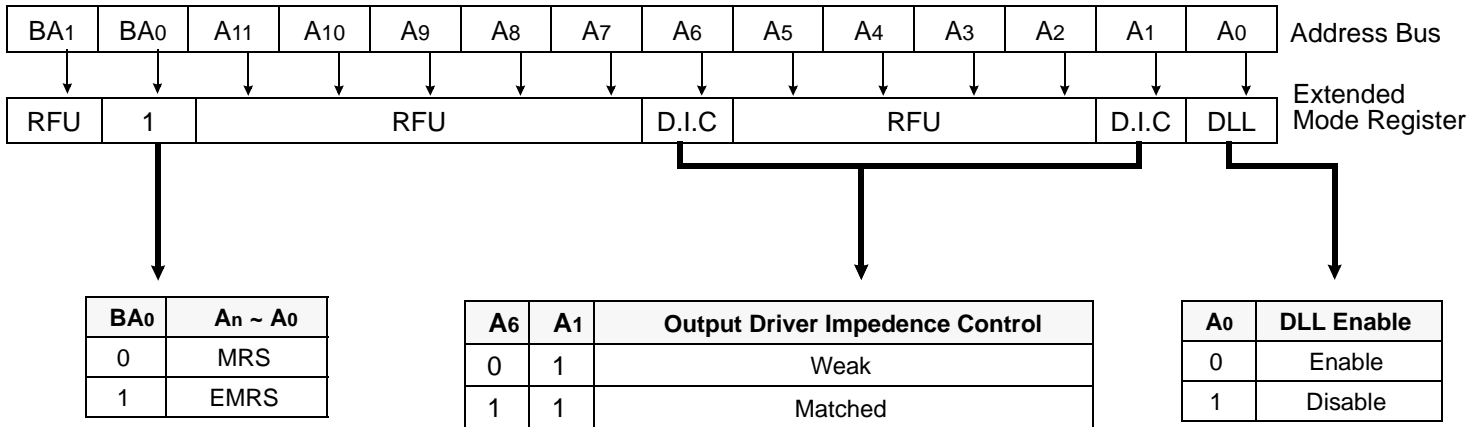


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**EXTENDED MODE REGISTER SET(EMRS)**

The extended mode register stores the data for enabling or disabling DLL and selecting output driver strength. The default value of the extended mode register is not defined, therefore the extended mode register must be written after power up for enabling or disabling DLL. The extended mode register is written by asserting low on CS, RAS, CAS, WE and high on BA0(The DDR SDRAM should be in all bank precharge with CKE already high prior to writing into the extended mode register). The state of address pins A0, A2 ~ A5, A7 ~ A11 and BA1 in the same cycle as CS, RAS, CAS and WE going low are written in the extended mode register. A1 and A6 are used for setting driver strength to normal, weak or matched impedance. Two clock cycles are required to complete the write operation in the extended mode register. The mode register contents can be changed using the same command and clock cycle requirements during operation as long as all banks are in the idle state. A0 is used for DLL enable or disable. "High" on BA0 is used for EMRS. All the other address pins except A0,A1,A6 and BA0 must be set to low for proper EMRS operation. Refer to the table for specific codes.



\*1 : RFU(Reserved for future use) should stay "0" during EMRS cycle.

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## ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Voltage on any pin relative to Vss	V <sub>IN</sub> , V <sub>OUT</sub>	-0.5 ~ 3.6	V
Voltage on VDD supply relative to Vss	VDD	-1.0 ~ 3.6	V
Voltage on VDD supply relative to Vss	VDDQ	-0.5 ~ 3.6	V
Storage temperature	T <sub>STG</sub>	-55 ~ +150	°C
Power dissipation	P <sub>D</sub>	2.0	W
Short circuit current	I <sub>OS</sub>	50	mA

**Note :** Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded.  
 Functional operation should be restricted to recommended operating condition.  
 Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

## POWER & DC OPERATING CONDITIONS(SSTL\_2 In/Out)

Recommended operating conditions(Voltage referenced to Vss=0V, TA=0 to 65°C)

Parameter	Symbol	Min	Typ	Max	Unit	Note
Device Supply voltage	VDD	2.375	2.50	2.625	V	1,7
Output Supply voltage	VDDQ	2.375	2.50	2.625	V	1,7
Reference voltage	VREF	0.49*VDDQ	-	0.51*VDDQ	V	2
Termination voltage	V <sub>tt</sub>	VREF-0.04	VREF	VREF+0.04	V	3
Input logic high voltage	V <sub>IH(DC)</sub>	VREF+0.15	-	VDDQ+0.30	V	4
Input logic low voltage	V <sub>IL(DC)</sub>	-0.30	-	VREF-0.15	V	5
Output logic high voltage	V <sub>OH</sub>	V <sub>tt</sub> +0.76	-	-	V	I <sub>OH</sub> =-15.2mA
Output logic low voltage	V <sub>OL</sub>	-	-	V <sub>tt</sub> -0.76	V	I <sub>OL</sub> =+15.2mA
Input leakage current	I <sub>IL</sub>	-5	-	5	uA	6
Output leakage current	I <sub>OL</sub>	-5	-	5	uA	6

- Note :**
- Under all conditions VDDQ must be less than or equal to VDD.
  - VREF is expected to equal 0.50\*VDDQ of the transmitting device and to track variations in the DC level of the same. Peak to peak noise on the VREF may not exceed + 2% of the DC value. Thus, from 0.50\*VDDQ, VREF is allowed + 25mV for DC error and an additional + 25mV for AC noise.
  - V<sub>tt</sub> of the transmitting device must track VREF of the receiving device.
  - V<sub>IH(max.)</sub>= VDDQ +1.5V for a pulse width and it can not be greater than 1/3 of the cycle rate.
  - V<sub>IL(mim.)</sub>= -1.5V for a pulse width and it can not be greater than 1/3 of the cycle rate.
  - For any pin under test input of 0V ≤ V<sub>IN</sub> ≤ VDD is acceptable. For all other pins that are not under test V<sub>IN</sub>=0V.
  - For the K4D261638E-TC2A, VDD & VDDQ = 2.8V±0.1V**

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## DC CHARACTERISTICS

Recommended operating conditions Unless Otherwise Noted, TA=0 to 65°C)

Parameter	Symbol	Test Condition	Version					Unit	Note
			-2A	-33	-36	-40	-50		
Operating Current (One Bank Active)	ICC1	Burst Lenth=2 trc ≥ trc(min) IOL=0mA, tcc= tcc(min)	TBD	210	200	190	170	mA	1
Precharge Standby Current in Power-down mode	ICC2P	CKE ≤ VIL(max), tcc= tcc(min)	TBD	70				mA	
Precharge Standby Current in Non Power-down mode	ICC2N	CKE ≥ VIH(min), CS ≥ VIH(min), tcc= tcc(min)	TBD	100	90	80	70	mA	
Active Standby Current power-down mode	ICC3P	CKE ≤ VIL(max), tcc= tcc(min)	TBD	80	75	70	65	mA	
Active Standby Current in in Non Power-down mode	ICC3N	CKE ≥ VIH(min), CS ≥ VIH(min), tcc= tcc(min)	TBD	150	140	130	120	mA	
Operating Current ( Burst Mode)	ICC4	trc ≥ trFC(min)trc ≥ trFC(min) Page Burst, All Banks activated.	TBD	380	360	340	320	mA	
Refresh Current	ICC5	trc ≥ trFC(min)	TBD	320	310	290	270	mA	2
Self Refresh Current	ICC6	CKE ≤ 0.2V	TBD	4				mA	

- Note :** 1. Measured with outputs open.  
2. Refresh period is 32ms.

## AC INPUT OPERATING CONDITIONS

Recommended operating conditions(Voltage referenced to VSS=0V, VDD=2.5V± 5%, VDDQ=2.5V± 5%,TA=0 to 65°C)

Parameter	Symbol	Min	Typ	Max	Unit	Note
Input High (Logic 1) Voltage; DQ	VIH	VREF+0.35	-	-	V	
Input Low (Logic 0) Voltage; DQ	VIL	-	-	VREF-0.35	V	
Clock Input Differential Voltage; CK and $\overline{CK}$	VID	0.7	-	VDDQ+0.6	V	1
Clock Input Crossing Point Voltage; CK and $\overline{CK}$	VIX	0.5*VDDQ-0.2	-	0.5*VDDQ+0.2	V	2

- Note :** 1. VID is the magnitude of the difference between the input level on CK and the input level on  $\overline{CK}$   
2. The value of Vix is expected to equal 0.5\*VDDQ of the transmitting device and must track variations in the DC level of the same  
**3. For the K4D261638E-TC2A, VDD & VDDQ = 2.8V±0.1V.**

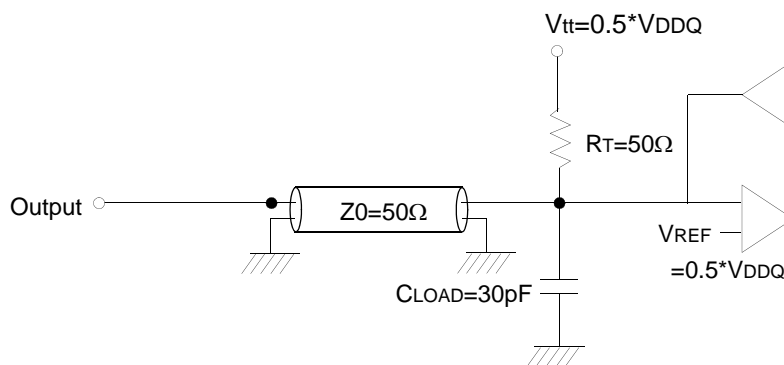
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## AC OPERATING TEST CONDITIONS (VDD=2.5V±5%, TA= 0 to 65°C)

Parameter	Value	Unit	Note
Input reference voltage for CK(for single ended)	0.50*VDDQ	V	
CK and $\overline{CK}$ signal maximum peak swing	1.5	V	
CK signal minimum slew rate	1.0	V/ns	
Input Levels(VIH/VIL)	VREF+0.35/VREF-0.35	V	
Input timing measurement reference level	VREF	V	
Output timing measurement reference level	Vtt	V	
Output load condition	See Fig.1		

1.For the K4D261638E-TC2A, VDD & VDDQ = 2.8V±0.1V.



(Fig. 1) Output Load Circuit

## CAPACITANCE (VDD=2.5V, TA= 25°C, f=1MHz)

Parameter	Symbol	Min	Max	Unit
Input capacitance( CK, $\overline{CK}$ )	CIN1	1.0	5.0	pF
Input capacitance(A0~A11, BA0~BA1)	CIN2	1.0	4.0	pF
Input capacitance (CKE, CS, RAS,CAS, WE )	CIN3	1.0	4.0	pF
Data & DQS input/output capacitance(DQ0~DQ15)	COUT	1.0	6.5	pF
Input capacitance(DM0 ~ DM3)	CIN4	1.0	6.5	pF

## DECOUPLING CAPACITANCE GUIDE LINE

Recommended decoupling capacitance added to power line at board.

Parameter	Symbol	Value	Unit
Decoupling Capacitance between VDD and VSS	CDC1	0.1 + 0.01	uF
Decoupling Capacitance between VDDQ and VSSQ	CDC2	0.1 + 0.01	uF

- Note :**
- VDD and VDDQ pins are separated each other.  
All VDD pins are connected in chip. All VDDQ pins are connected in chip.
  - VSS and VSSQ pins are separated each other  
All VSS pins are connected in chip. All VSSQ pins are connected in chip.

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**AC CHARACTERISTICS**

Parameter	Sym- bol	-2A		-33		-36		-40		-50		Unit	Note	
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max			
CK cycle time	CL=3	tCK	-	10	-	10	-	10	4.0	10	5.0	10	ns	
	CL=4	tCK	2.86		3.3		3.6		-		-		ns	
CK high level width		tCH	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	tCK	
CK low level width		tCL	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	tCK	
DQS out access time from CK		tDQSCK	-0.6	0.6	-0.6	0.6	-0.6	0.6	-0.6	0.6	-0.7	0.7	ns	
Output access time from CK		tAC	-0.6	0.6	-0.6	0.6	-0.6	0.6	-0.6	0.6	-0.7	0.7	ns	
Data strobe edge to Dout edge		tDQSQ	-	0.35	-	0.35	-	0.40	-	0.4	-	0.45	ns	1
Read preamble		tRPRE	0.9	1.1	0.9	1.1	0.9	1.1	0.9	1.1	0.9	1.1	tCK	
Read postamble		tRPST	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	tCK	
CK to valid DQS-in		tDQSS	0.85	1.15	0.85	1.15	0.85	1.15	0.85	1.15	0.8	1.2	tCK	
DQS-In setup time		tWPRES	0	-	0	-	0	-	0	-	0	-	ns	
DQS-in hold time		tWPREH	0.35	-	0.35	-	0.35	-	0.35	-	0.3	-	tCK	
DQS write postamble		tWPST	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	tCK	
DQS-In high level width		tDQSH	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	tCK	
DQS-In low level width		tDQSL	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	tCK	
Address and Control input setup		tIS	0.9	-	0.9	-	0.9	-	0.9	-	1.0	-	ns	
Address and Control input hold		tIH	0.9	-	0.9	-	0.9	-	0.9	-	1.0	-	ns	
DQ and DM setup time to DQS		tDS	0.35	-	0.35	-	0.40	-	0.4	-	0.45	-	ns	
DQ and DM hold time to DQS		tDH	0.35	-	0.35	-	0.40	-	0.4	-	0.45	-	ns	
Clock half period		tHP	tCLmin or tCHmin	-	tCLmin or tCHmin	-	tCLmin or tCHmin	-	tCLmin or tCHmin	-	tCLmin or tCHmin	-	ns	1
Data output hold time from DQS		tQH	tHP- 0.35	-	tHP- 0.35	-	tHP-0.4	-	tHP-0.4	-	tHP- 0.45	-	ns	1

Note 1 :

- The JEDEC DDR specification currently defines the output data valid window(tDV) as the time period when the data strobe and all data associated with that data strobe are coincidentally valid.
- The previously used definition of tDV(=0.35tCK) artificially penalizes system timing budgets by assuming the worst case output valid window even then the clock duty cycle applied to the device is better than 45/55%
- A new AC timing term, tQH which stands for data output hold time from DQS is defined to account for clock duty cycle variation and replaces tDV
- tQHmin = tHP-X where
  - . tHP=Minimum half clock period for any given cycle and is defined by clock high or clock low time(tCH,tCL)
  - . X=A frequency dependent timing allowance account for tDQSQmax

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**AC CHARACTERISTICS (I)**

Parameter	Symbol	-2A		-33		-36		-40		-50		Unit	Note
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Row cycle time	tRC	15	-	15	-	15	-	13	-	12	-	tCK	
Refresh row cycle time	tRFC	17	-	17	-	17	-	15	-	14	-	tCK	
Row active time	tRAS	10	100K	10	100K	10	100K	9	100K	8	100K	tCK	
RAS to CAS delay for Read	tRCDRD	4	-	4	-	4	-	4	-	4	-	tCK	
RAS to CAS delay for Write	tRCDWR	2	-	2	-	2	-	2	-	2	-	tCK	
Row precharge time	tRP	5	-	5	-	5	-	4	-	4	-	tCK	
Row active to Row active	tRRD	3	-	3	-	3	-	3	-	3	-	tCK	
Last data in to Row precharge @Normal Precharge	tWR	3	-	3	-	3	-	3	-	3	-	tCK	1
Last data in to Row precharge @Auto Precharge	tWR_A	3	-	3	-	3	-	3	-	3	-	tCK	1
Last data in to Read command	tCDLR	3	-	3	-	2	-	2	-	2	-	tCK	1
Col. address to Col. address	tCCD	1	-	1	-	1	-	1	-	1	-	tCK	
Mode register set cycle time	tMRD	2	-	2	-	2	-	2	-	2	-	tCK	
Auto precharge write recovery + Precharge	tDAL	8	-	8	-	8	-	7	-	7	-	tCK	
Exit self refresh to read command	tXSR	200	-	200	-	200	-	200	-	200	-	tCK	
Power down exit time	tPDEX	3tCK +tIS	-	3tCK +tIS	-	3tCK +tIS	-	3tCK +tIS	-	3tCK +tIS	-	ns	
Refresh interval time	tREF	7.8	-	7.8	-	7.8	-	7.8	-	7.8	-	us	

Note : 1. For normal write operation, even numbers of Din are to be written inside DRAM

**AC CHARACTERISTICS (II)**

(Unit : Number of Clock)

**K4D261638E-TC2A**

Frequency	Cas Latency	tRC	tRFC	tRAS	tRCDRD	tRCDWR	tRP	tRRD	tDAL	Unit
350MHz ( 2.86ns )	4	15	17	10	4	2	5	3	8	tCK
300MHz ( 3.3ns )	4	15	17	10	4	2	5	3	8	tCK
275MHz ( 3.6ns )	4	15	17	10	4	2	5	3	8	tCK
250MHz ( 4.0ns )	3	13	15	9	4	2	4	3	7	tCK
200MHz ( 5.0ns )	3	12	14	8	4	2	4	3	7	tCK

**K4D261638E-TC33**

Frequency	Cas Latency	tRC	tRFC	tRAS	tRCDRD	tRCDWR	tRP	tRRD	tDAL	Unit
300MHz ( 3.3ns )	4	15	17	10	4	2	5	3	8	tCK
275MHz ( 3.6ns )	4	15	17	10	4	2	5	3	8	tCK
250MHz ( 4.0ns )	3	13	15	9	4	2	4	3	7	tCK
200MHz ( 5.0ns )	3	12	14	8	4	2	4	3	7	tCK

# K4D261638E

# 128M DDR SDRAM

## K4D261638E-TC36

Frequency	Cas Latency	tRC	tRFC	tRAS	tRCDRD	tRCDWR	tRP	tRRD	tDAL	Unit
275MHz ( 3.6ns )	4	15	17	10	4	2	5	3	8	tCK
250MHz ( 4.0ns )	3	13	15	9	4	2	4	3	7	tCK
200MHz ( 5.0ns )	3	12	14	8	4	2	4	3	7	tCK

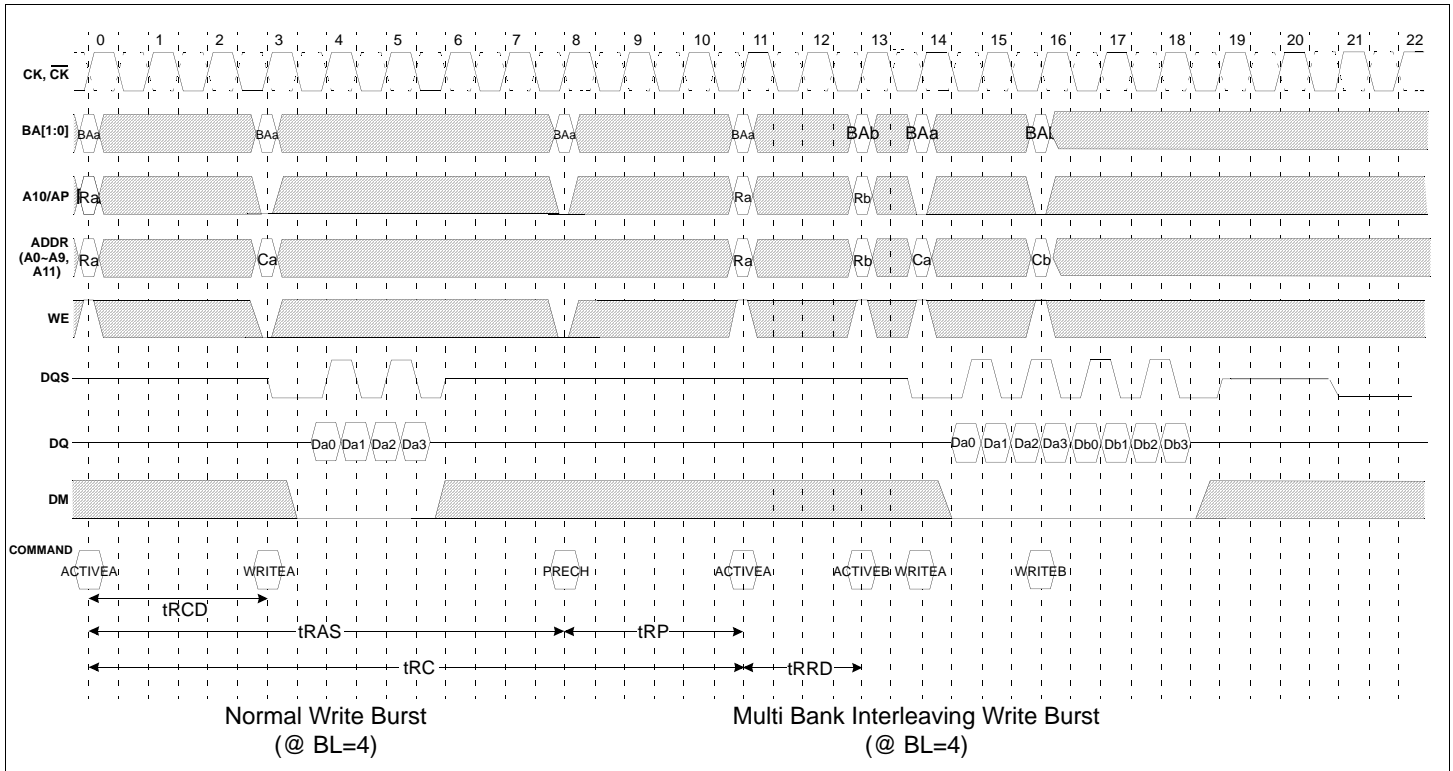
## K4D261638E-TC40

Frequency	Cas Latency	tRC	tRFC	tRAS	tRCDRD	tRCDWR	tRP	tRRD	tDAL	Unit
250MHz ( 4.0ns )	3	13	15	9	4	2	4	3	7	tCK
200MHz ( 5.0ns )	3	12	14	8	4	2	4	3	7	tCK

## K4D261638E-TC50

Frequency	Cas Latency	tRC	tRFC	tRAS	tRCDRD	tRCDWR	tRP	tRRD	tDAL	Unit
200MHz ( 5.0ns )	3	12	14	8	4	2	4	3	7	tCK

## Simplified Timing @ BL=4



**K4D261638E**

**128M DDR SDRAM**

**PACKAGE DIMENSIONS (66pin TSOP-II)**

